Micro Commercial Components
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BU910

NPN Silicon Power Transistors

Features

- With TO-220 package
- Particularly designed for applications such as electronic ignition.

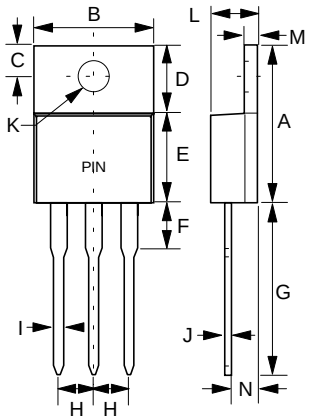
Maximum Ratings

Symbol	Rating	Rating	Unit
V_{CEO}	Collector-Emitter Voltage	350	V
V_{CBO}	Collector-Base Voltage	400	V
V_{EBO}	Emitter to Base Voltage	5.0	V
I_{CP}	Peak Collector Current	10	A
I_C	Collector Current	6.0	A
P_C	Collector power dissipation	60	W
T_J	Junction Temperature	-55 to +150	^{O}C
T_{STG}	Storage Temperature	-55 to +150	^{O}C

Electrical Characteristics @ 25^{O}C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
OFF CHARACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage (I_C=100mAdc, I_B=0)	350	---	Vdc
I_{CBO}	Collector-Base Cutoff Current (V_{CB}=400Vdc,I_E=0)	---	1.0	mAdc
I_{EBO}	Emitter-Base Cutoff Current (V_{EB}=5.0Vdc, I_C=0)	---	5.0	mAdc
I_{CEO}	Collector-Emitter Cutoff Current (V_{CE}=350Vdc, I_B=0)	---	1.0	mAdc
ON CHARACTERISTICS				
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage (I_C=2.5Adc, I_B=50mAdc)	---	1.8	Vdc
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage (I_C=4.0Adc, I_B=200mAdc)	---	1.8	Vdc
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage (I_C=2.5Adc, I_B=50mAdc)	---	2.2	Vdc
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage (I_C=4.0Adc, I_B=200mAdc)	---	2.5	Vdc

TO-220



DIMENSIONS					
	INCHES		MM		
DIM	MIN	MAX	MIN	MAX	NOTE
A	.560	.625	14.22	15.88	
B	.380	.420	9.65	10.67	
C	.100	.135	2.54	3.43	
D	.230	.270	5.84	6.86	
E	.380	.420	9.65	10.67	
F	------	.250	------	6.35	
G	.500	.580	12.70	14.73	
H	.090	.110	2.29	2.79	
I	.020	.045	0.51	1.14	
J	.012	.025	0.30	0.64	
K	.139	.161	3.53	4.09	∅
L	.140	.190	3.56	4.83	
M	.045	.055	1.14	1.40	
N	.080	.115	2.03	2.92	